

# Wing Man Tang

## List of Publications by Year in descending order

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124  
papers

3,485  
citations

331670

21  
h-index

144013

57  
g-index

125  
all docs

125  
docs citations

125  
times ranked

6257  
citing authors

| #  | ARTICLE   | IF   | CITATIONS |
|----|---|------|-----------|
| 1  | Universal energy-level alignment of molecules on metal oxides. <i>Nature Materials</i> , 2012, 11, 76-81.   | 27.5 | 836       |
| 2  | Transition Metal Oxide Work Functions: The Influence of Cation Oxidation State and Oxygen Vacancies. <i>Advanced Functional Materials</i> , 2012, 22, 4557-4568.  | 14.9 | 694       |
| 3  | Metal/Metal-Oxide Interfaces: How Metal Contacts Affect the Work Function and Band Structure of $\text{MoO}_3$ . <i>Advanced Functional Materials</i> , 2013, 23, 215-226.                                | 14.9 | 326       |
| 4  | Effects of Processing Conditions on the Work Function and Energy-Level Alignment of NiO Thin Films. <i>Journal of Physical Chemistry C</i> , 2010, 114, 19777-19781.                                      | 3.1  | 176       |
| 5  | Work function of fluorine doped tin oxide. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2011, 29, .  | 2.1  | 163       |
| 6  | High-performance fiber-shaped supercapacitors using carbon fiber thread (CFT)@polyaniline and functionalized CFT electrodes for wearable/stretchable electronics. <i>Nano Energy</i> , 2015, 11, 662-670. | 16.0 | 134       |
| 7  | A metallic molybdenum suboxide buffer layer for organic electronic devices. <i>Applied Physics Letters</i> , 2010, 96, .  | 3.3  | 82        |
| 8  | Aqueous Manganese Dioxide Ink for Paper-Based Capacitive Energy Storage Devices. <i>Angewandte Chemie - International Edition</i> , 2015, 54, 6800-6803.  | 13.8 | 69        |
| 9  | Highly flexible and transferable supercapacitors with ordered three-dimensional $\text{MnO}_2/\text{Au}/\text{MnO}_2$ nanospine arrays. <i>Journal of Materials Chemistry A</i> , 2015, 3, 10199-10204.   | 10.3 | 53        |
| 10 | Electrochemical characteristics of amorphous silicon carbide film as a lithium-ion battery anode. <i>RSC Advances</i> , 2018, 8, 5189-5196.   | 3.6  | 51        |
| 11 | Effects of Ta incorporation in $\text{La}_2\text{O}_3$ gate dielectric of InGaZnO thin-film transistor. <i>Applied Physics Letters</i> , 2014, 104, .   | 3.3  | 45        |
| 12 | Controllable functionalized carbon fabric for high-performance all-carbon-based supercapacitors. <i>RSC Advances</i> , 2014, 4, 33022.  | 3.6  | 40        |
| 13 | Improved performance of asymmetric fiber-based micro-supercapacitors using carbon nanoparticles for flexible energy storage. <i>Journal of Materials Chemistry A</i> , 2015, 3, 15633-15641.              | 10.3 | 33        |
| 14 | Suppressing the Coffee-Ring Effect in Semitransparent $\text{MnO}_2$ Film for a High-Performance Solar-Powered Energy Storage Window. <i>ACS Applied Materials &amp; Interfaces</i> , 2016, 8, 9088-9096. | 8.0  | 26        |
| 15 | High-mobility pentacene thin-film transistor by using $\text{La}_x\text{Ta}_{(1-x)}\text{O}_y$ as gate dielectric. <i>Organic Electronics</i> , 2014, 15, 2499-2504.                                      | 2.6  | 25        |
| 16 | Effects of UV-ozone treatment on radio-frequency magnetron sputtered ZnO thin films. <i>Thin Solid Films</i> , 2011, 520, 569-573.  | 1.8  | 24        |
| 17 | Advances in La-Based High-k Dielectrics for MOS Applications. <i>Coatings</i> , 2019, 9, 217.   | 2.6  | 24        |
| 18 | High-performance organic thin-film transistor by using $\text{LaNbO}$ as gate dielectric. <i>Applied Physics Letters</i> , 2015, 107, .   | 3.3  | 23        |

| #  | ARTICLE   | IF  | CITATIONS |
|----|---|-----|-----------|
| 19 | Few-Layered MoS <sub>2</sub> Field-Effect Transistors with a Vertical Channel of Sub-10 nm. ACS Applied Materials & Interfaces, 2020, 12, 32943-32950.  | 8.0 | 23        |
| 20 | Improved Electrical Performance of Multilayer MoS <sub>2</sub> Transistor With NH <sub>3</sub> -Annealed ALD HfTiO Gate Dielectric. IEEE Transactions on Electron Devices, 2017, 64, 1020-1025.                                 | 3.0 | 22        |
| 21 | A Study on Pentacene Organic Thin-Film Transistor With Different Gate Materials on Various Substrates. IEEE Electron Device Letters, 2017, 38, 744-747.   | 3.9 | 21        |
| 22 | High-Mobility Pentacene Organic Thin-Film Transistor with La <sub>2</sub> NbO <sub>7</sub> Dielectric Fabricated on Vacuum Tape. IEEE Transactions on Electron Devices, 2017, 64, 1716-1722.                                    | 3.9 | 19        |
| 23 | Influence of Gate Doping Concentration on the Characteristics of Amorphous InGaZnO Thin-Film Transistors With HfLaO Gate Dielectric. IEEE Electron Device Letters, 2019, 40, 1953-1956.   | 3.9 | 18        |
| 24 | A Study on La Incorporation in Transition-Metal (Y, Zr, and Nb) Oxides as Gate Dielectric of Pentacene Organic Thin-Film Transistor. IEEE Transactions on Electron Devices, 2015, 62, 2313-2319.                                | 3.0 | 17        |
| 25 | Correlation between carrier mobility of pentacene thin-film transistor and surface passivation of its gate dielectric. Journal of Applied Physics, 2008, 104, .   | 2.5 | 16        |
| 26 | Nitrided HfTiON/Ga <sub>2</sub> O <sub>3</sub> (Gd <sub>2</sub> O <sub>3</sub> ) as stacked gate dielectric for GaAs MOS applications. Applied Physics Express, 2014, 7, 061201.  | 2.4 | 15        |
| 27 | High-Performance Pentacene Thin-Film Transistor With High- $\kappa$ HfLaON as Gate Dielectric. IEEE Electron Device Letters, 2013, 34, 1397-1399.   | 3.9 | 13        |
| 28 | On the voltage dependence of sensitivity for Schottky-type gas sensor. Applied Physics Letters, 2014, 105, 223503.  | 3.3 | 13        |
| 29 | Improved Characteristics of InGaZnO Thin-Film Transistor by Using Fluorine Implant. ECS Solid State Letters, 2014, 3, P87-P90.  | 1.4 | 13        |
| 30 | Improved Interfacial and Electrical Properties of GaAs MOS Capacitor With LaON/TiON Multilayer Composite Gate Dielectric and LaON as Interfacial Passivation Layer. IEEE Transactions on Electron Devices, 2017, 64, 1535-1540. | 3.0 | 13        |
| 31 | High-performance pentacene OTFT by incorporating Ti in LaON gate dielectric. Applied Physics Letters, 2017, 111, .  | 3.3 | 13        |
| 32 | Working Principle of Hydrogen Sensor Based on Pentacene Thin-Film Transistor. IEEE Electron Device Letters, 2017, 38, 1132-1135.  | 3.9 | 13        |
| 33 | Effects of Metal-Hydroxyl and InO Defects on Performance of InGaZnO Thin-Film Transistor. IEEE Transactions on Electron Devices, 2018, 65, 1009-1013.   | 3.0 | 13        |
| 34 | Effects of Gate Electron Concentration on the Performance of Pentacene Organic Thin-Film Transistors. IEEE Electron Device Letters, 2018, 39, 963-966.  | 3.9 | 13        |
| 35 | Improved interfacial quality of GaAs metal-oxide-semiconductor device with NH <sub>3</sub> -plasma treated yttrium-oxynitride as interfacial passivation layer. Microelectronics Reliability, 2016, 56, 17-21.                  | 1.7 | 12        |
| 36 | Enhanced hydrogen-sensing characteristics of MISiC Schottky-diode hydrogen sensor by trichloroethylene oxidation. Sensors and Actuators A: Physical, 2005, 119, 63-67.  | 4.1 | 11        |

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|----|---|-----|-----------|
| 37 | Effects of N <sub>2</sub> -annealing conditions on the sensing properties of Pt/HfO <sub>2</sub> /SiC Schottky-diode hydrogen sensor. <i>Thin Solid Films</i> , 2010, 519, 505-511.   | 1.8 | 11        |
| 38 | Plasma-Nitrided Ga <sub>2</sub> O <sub>3</sub> (Gd <sub>2</sub> O <sub>3</sub> ) as Interfacial Passivation Layer for InGaAs Metal-oxide Semiconductor Capacitor With HfTiON Gate Dielectric. <i>IEEE Transactions on Electron Devices</i> , 2015, 62, 1235-1240. | 3.0 | 11        |
| 39 | Effects of annealing on electrical performance of multilayer MoS <sub>2</sub> transistors with atomic layer deposited HfO <sub>2</sub> gate dielectric. <i>Applied Physics Express</i> , 2016, 9, 095202.   | 2.4 | 11        |
| 40 | Schottky-diode hydrogen sensor based on InGaN/GaN multiple quantum wells. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014, 32, 011212.  | 1.2 | 10        |
| 41 | Influences of Remote Coulomb and Interface-Roughness Scatterings on Electron Mobility of InGaAs MOSFET With High-k Stacked Gate Dielectric. <i>IEEE Nanotechnology Magazine</i> , 2015, 14, 854-861.  | 2.0 | 10        |
| 42 | A comparative study of Hf and Ta incorporations in the dielectric of Pd-WO <sub>3</sub> -SiC Schottky-diode hydrogen sensor. <i>Sensors and Actuators B: Chemical</i> , 2018, 259, 725-729.   | 7.8 | 10        |
| 43 | Gate Screening on Remote Phonon Scattering for Pentacene Organic TFTs: Holes Versus Electrons. <i>IEEE Electron Device Letters</i> , 2019, 40, 893-896.   | 3.9 | 10        |
| 44 | High-mobility pentacene organic thin-film transistors achieved by reducing remote phonon scattering and surface-roughness scattering. <i>Applied Surface Science</i> , 2021, 544, 148656.   | 6.1 | 10        |
| 45 | Improved sensing characteristics of MISiC Schottky-diode hydrogen sensor by using HfO <sub>2</sub> as gate insulator. <i>Microelectronics Reliability</i> , 2008, 48, 1780-1785.  | 1.7 | 9         |
| 46 | Effects of interfacial oxide layers of the electrode metals on the electrical characteristics of organic thin-film transistors with HfO <sub>2</sub> gate dielectric. <i>Journal of Applied Physics</i> , 2011, 110, 044108.                                      | 2.5 | 9         |
| 47 | Improved interfacial and electrical properties of HfLaON gate dielectric Ge MOS capacitor by NbON/Si dual passivation layer and fluorine incorporation. <i>Applied Physics Letters</i> , 2016, 109, .   | 3.3 | 9         |
| 48 | GaAs Metal-oxide Semiconductor Capacitor With Nd-Based High-k Oxynitrides as Gate Dielectric and Passivation Layer. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 72-78.   | 3.0 | 9         |
| 49 | Effects of Trapped Charges in Gate Dielectric and High-k Encapsulation on Performance of MoS <sub>2</sub> Transistor. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 1107-1112.   | 3.0 | 9         |
| 50 | Reduced screening of remote phonon scattering in thin-film transistors caused by gate-electrode/gate-dielectric interlayer. <i>Applied Physics Letters</i> , 2020, 117, .   | 3.3 | 9         |
| 51 | Determination of optimal insulator thickness for MISiC hydrogen sensors. <i>Solid-State Electronics</i> , 2004, 48, 1673-1677.  | 1.4 | 8         |
| 52 | Enhanced Sensing Performance of MISiC Schottky-Diode Hydrogen Sensor by Using HfON as Gate Insulator. <i>IEEE Sensors Journal</i> , 2011, 11, 2940-2946.  | 4.7 | 8         |
| 53 | UV ozone passivation of the metal/dielectric interface for HfO <sub>2</sub> -based organic thin film transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010, 28, 1100-1103.                                   | 1.2 | 7         |
| 54 | Electrical and Interfacial Properties of GaAs MOS Capacitors With La-Doped ZrON as Interfacial Passivation Layer. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 2179-2184.   | 3.0 | 7         |

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|----|--|-----|-----------|
| 55 | Improved Sensing Characteristics of a Novel $\text{Pt}/\text{HfTiO}_2/\text{SiC}$ Schottky-Diode Hydrogen Sensor. IEEE Transactions on Electron Devices, 2012, 59, 2818-2824.  | 3.0 | 6         |
| 56 | Interfacial and electrical properties of InGaAs metal-oxide-semiconductor capacitor with TiON/TaON multilayer composite gate dielectric. Applied Physics Letters, 2015, 106, 123504.   | 3.3 | 6         |
| 57 | Improved performance of Pd/WO <sub>3</sub> /SiC Schottky-diode hydrogen gas sensor by using fluorine plasma treatment. Applied Physics Letters, 2015, 107, .   | 3.3 | 6         |
| 58 | Impact of Nitrogen Incorporation on the Interface Between Ge and La <sub>2</sub> O <sub>3</sub> or Y <sub>2</sub> O <sub>3</sub> Gate Dielectric: A Study on the Formation of Germanate. IEEE Transactions on Electron Devices, 2016, 63, 4888-4892. | 3.0 | 6         |
| 59 | N <sub>2</sub> -Plasma-Treated Ga <sub>2</sub> O <sub>3</sub> (Gd <sub>2</sub> O <sub>3</sub> ) as Interface Passivation Layer for Ge MOS Capacitor With HfTiON Gate Dielectric. IEEE Transactions on Electron Devices, 2016, 63, 2838-2843.         | 3.0 | 6         |
| 60 | High-Performance Pentacene Organic Thin-Film Transistor by Using Nd <sub>2</sub> O <sub>3</sub> Gate Dielectric Doped with Nb. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700609.                                     | 1.8 | 6         |
| 61 | A Study on Organic Thin-Film Transistors Using Hf-La Oxides With Different La Contents as Gate Dielectrics. IEEE Transactions on Electron Devices, 2018, 65, 1107-1112.  | 3.0 | 6         |
| 62 | Double-Layer MnCo <sub>2</sub> S <sub>4</sub> @Ni-Co-S Core/Shell Nanostructure on Nickel Foam for High-Performance Supercapacitor. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800147.                                | 1.8 | 6         |
| 63 | Effects of a Gate-Electrode/Gate-Dielectric Interlayer on Carrier Mobility for Pentacene Organic Thin-Film Transistors. IEEE Electron Device Letters, 2018, 39, 1516-1519.   | 3.9 | 6         |
| 64 | Simulation Study of 4H-SiC High-k Pillar MOSFET With Integrated Schottky Barrier Diode. IEEE Journal of the Electron Devices Society, 2021, 9, 951-957.  | 2.1 | 6         |
| 65 | Split-Drain Magnetic Field-Effect Transistor Channel Charge Trapping and Stress Induced Sensitivity Deterioration. IEEE Transactions on Magnetics, 2014, 50, 1-4.  | 2.1 | 5         |
| 66 | Improved interfacial and electrical properties of Ge MOS capacitor by using TaON/LaON dual passivation interlayer. Applied Physics Letters, 2016, 109, .   | 3.3 | 5         |
| 67 | Improvements of Interfacial and Electrical Properties for Ge MOS Capacitor by Using TaYON Interfacial Passivation Layer and Fluorine Incorporation. IEEE Transactions on Electron Devices, 2017, 64, 3528-3533.                                      | 3.0 | 5         |
| 68 | Plasmon-phonon resonance at gate-electrode/gate-dielectric interface on carrier mobility of organic TFTs with high-k gate dielectrics. Applied Surface Science, 2021, 565, 150374.   | 6.1 | 5         |
| 69 | A Comparison of MISiC Schottky-Diode Hydrogen Sensors Made by NO <sub>2</sub> , N <sub>2</sub> O, or NH <sub>3</sub> Nitridations. IEEE Transactions on Electron Devices, 2006, 53, 2378-2383.   | 3.0 | 4         |
| 70 | Equivalent distributed capacitance model of oxide traps on frequency dispersion of $C \sim V$ curve for MOS capacitors. Chinese Physics B, 2016, 25, 118502.   | 1.4 | 4         |
| 71 | Hydrogen sensor based on pentacene thin-film transistor. , 2016, , .   |     | 4         |
| 72 | Improved Interfacial and Electrical Properties of GaAs Metal-Oxide-Semiconductor Capacitor by Using Fluorine-Plasma-Treated Interfacial Passivation Layer. IEEE Transactions on Device and Materials Reliability, 2017, 17, 458-462.                 | 2.0 | 4         |

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|----|---|-----|-----------|
| 73 | Repair of Oxygen Vacancies and Improvement of HfO <sub>2</sub> /MoS <sub>2</sub> Interface by NH <sub>3</sub> -Plasma Treatment. IEEE Transactions on Electron Devices, 2019, 66, 4337-4342.  | 3.0 | 4         |
| 74 | Improved Interfacial and Electrical Properties of MoS <sub>2</sub> Transistor With High/Low-Temperature Grown Hf <sub>0.5</sub> Al <sub>0.5</sub> O <sub>2</sub> as Top-Gate Dielectric. IEEE Electron Device Letters, 2020, 41, 385-388. | 3.9 | 4         |
| 75 | Enhanced screening on remote phonon scattering in InGaZnO thin-film transistor by using Ge gate electrode. Journal of Applied Physics, 2021, 130, .   | 2.5 | 4         |
| 76 | Anti-Screening Effect of Gate-Electrode Holes on Remote Phonon Scattering in InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2022, 69, 174-179.   | 3.0 | 4         |
| 77 | Low-Temperature-Processed High-Performance Pentacene OTFTs with Optimal Nd-Ti Oxynitride Mixture as Gate Dielectric. Materials, 2022, 15, 2255.   | 2.9 | 4         |
| 78 | Effects of Annealing Time on the Performance of OTFT on Glass with ZrO <sub>2</sub> as Gate Dielectric. Active and Passive Electronic Components, 2012, 2012, 1-5.  | 0.3 | 3         |
| 79 | Comparison of CuPc-based organic thin-film transistors made by different dielectric structures. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, 012201.  | 1.2 | 3         |
| 80 | High-mobility pentacene OTFT with TaLaO gate dielectric passivated by fluorine plasma. Physica Status Solidi - Rapid Research Letters, 2014, 8, 866-870.  | 2.4 | 3         |
| 81 | Analytical modeling of nonideal Schottky diode with series and shunt resistance and application in hydrogen gas sensors. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2764-2768.                              | 1.8 | 3         |
| 82 | Improved interfacial and electrical properties of Ge MOS capacitor with ZrON/TaON multilayer composite gate dielectric by using fluorinated Si passivation layer. Applied Physics Letters, 2017, 111, 053501.                             | 3.3 | 3         |
| 83 | Fabrication and electrical performance of CVD-grown MoS <sub>2</sub> transistor. , 2017, , .  |     | 3         |
| 84 | Hydrogen sensors based on TFTs with catalytic source/drain electrodes: IGZO vs. pentacene. IEEE Electron Device Letters, 2018, , 1-1.   | 3.9 | 3         |
| 85 | Temperature Dependence of Sensing Characteristics for OTFT-Based Hydrogen Sensor. IEEE Transactions on Electron Devices, 2020, 67, 1776-1780.   | 3.0 | 3         |
| 86 | Dependence of sensing performance of OTFT-based H <sub>2</sub> sensor on channel length. International Journal of Hydrogen Energy, 2021, 46, 16232-16240.   | 7.1 | 3         |
| 87 | Sensing characteristics of a novel MISiC Schottky-diode hydrogen sensor with HfO <sub>2</sub> as gate insulator. , 2007, , .  |     | 2         |
| 88 | Pentacene thin-film transistors with HfO <sub>2</sub> gate dielectric annealed in NH <sub>3</sub> or N <sub>2</sub> O. , 2008, , .  |     | 2         |
| 89 | A novel hydrogen sensor based on Pt/WO <sub>3</sub> /Si MIS Schottky diode. , 2013, , .   |     | 2         |
| 90 | Thermal stability of sectorial split-drain magnetic field-effect transistors. Microelectronics Reliability, 2014, 54, 1115-1118.  | 1.7 | 2         |

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|-----|--|-----|-----------|
| 91  | Pentacene organic thin-film transistor with HfYO gate dielectric made on adhesive vacuum tape. Electronics Letters, 2015, 51, 644-646.   | 1.0 | 2         |
| 92  | Interfacial and Electrical Properties of Ge MOS Capacitor by ZrLaON Passivation Layer and Fluorine Incorporation. IOP Conference Series: Materials Science and Engineering, 2017, 229, 012018.   | 0.6 | 2         |
| 93  | Effects of Catalytic-Electrode Thickness on a Hydrogen Sensor Based on Organic Thin-Film Transistor. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700786.           | 1.8 | 2         |
| 94  | Hydrogen Sensor Based on Pentacene Organic Thin-Film Transistor for Flexible Applications. , 2018, , .   |     | 2         |
| 95  | Flexible Solid-state Supercapacitors Using Paper-based Electrodes for Energy Storage. , 2018, , .  |     | 2         |
| 96  | Surface Passivation Using Lanthanide Oxynitrides for GaAs Metal-Oxide-Semiconductor Applications. IEEE Transactions on Electron Devices, 2019, 66, 3080-3085.                                    | 3.0 | 2         |
| 97  | Influence of Source/Drain Catalytic Metal and Fabrication Method on OTFT-Based Hydrogen Sensor. IEEE Transactions on Electron Devices, 2022, 69, 2038-2042.                                      | 3.0 | 2         |
| 98  | Improved Performance for OTFT with HfTiO <sub>2</sub> as gate dielectric by N <sub>2</sub> O annealing. , 2007, , .  |     | 1         |
| 99  | Electrode effects on the breakdown characteristics of high-k HfO <sub>2</sub> . , 2010, , .  |     | 1         |
| 100 | Improved hydrogen-sensing performance of Pd/WO <sub>3</sub> /SiC Schottky diode by La doping. , 2016, , .  |     | 1         |
| 101 | Improved characteristics for OTFT with HfO <sub>2</sub> gate dielectric by using chlorinated indium tin oxide gate electrode. , 2016, , .  |     | 1         |
| 102 | A 2-D analytical threshold-voltage model for GeOI/GeON MOSFET with high-k gate dielectric. Microelectronics Reliability, 2016, 57, 24-33.  | 1.7 | 1         |
| 103 | Effective passivation of HfO <sub>2</sub> /Ge interface by using nitrated germanate as passivation interlayer. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600974. | 1.8 | 1         |
| 104 | Improved performance of pentacene OTFT by incorporating Ti in NdON gate dielectric. , 2017, , .  |     | 1         |
| 105 | Improved carrier mobility of pentacene organic TFTs by suppressed oxide growth at remote interface using nitrogen doping in high-k NdNbO dielectric. Organic Electronics, 2022, 102, 106427.     | 2.6 | 1         |
| 106 | Sensing characteristics of a novel NH <sub>3</sub> -nitrided Schottky-diode hydrogen sensor. , 2004, , .   |     | 0         |
| 107 | Effects of gate-insulator nitridation gas on MISiC Schottky-diode hydrogen sensors. , 0, , .   |     | 0         |
| 108 | Effects of annealing temperature on sensing properties of Pt/HfO <sub>2</sub> /SiC Schottky-diode hydrogen sensor. , 2008, , .   |     | 0         |

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|-----|---|----|-----------|
| 109 | Effects of Insulator Thickness on the Sensing Properties of MISiC Schottky-Diode Hydrogen Sensor. , 2008, , .   |    | 0         |
| 110 | Enhanced performance for OTFT on glass with HfO <sub>2</sub> as gate dielectric by UV-ozone treatment. , 2009, , .  |    | 0         |
| 111 | Effects of different Ar/O <sub>2</sub> ratios on the electrical properties of CuPc-based TFTs with ZrO <sub>2</sub> gate dielectric. , 2011, , .                      |    | 0         |
| 112 | Electrical properties of CuPc-based OTFTs with atomic layer deposited HfAlO gate dielectric. , 2012, , .  |    | 0         |
| 113 | Effects of fluorine plasma and ammonia annealing on pentacene thin-film transistor with HfTiO as gate dielectric. , 2013, , .   |    | 0         |
| 114 | A study on the electrical characteristics of copper phthalocyanine-based OTFTs with ZrTaO as gate dielectric. , 2013, , .   |    | 0         |
| 115 | Flexible solid-state fiber-shaped supercapacitors based on organic-inorganic hybrid electrodes for wearable energy storage. , 2014, , .                               |    | 0         |
| 116 | Thermal annealing effect on electrical characteristics of CuPc thin-film transistors on glass with ZrO <sub>2</sub> as gate dielectric. , 2015, , .                   |    | 0         |
| 117 | Electrical performance of multilayer MoS <sub>2</sub> transistor with ALD HfTiO gate dielectric. , 2016, , .  |    | 0         |
| 118 | A study on MnCo <sub>2</sub> S <sub>4</sub> @NiCo(OH) <sub>2</sub> core-shell nanocomposite for high-performance solid-state supercapacitor applications. , 2017, , . |    | 0         |
| 119 | Low-voltage otft-based H2 sensor fabricated on vacuum tape. , 2017, , .   |    | 0         |
| 120 | Improved Performance of Pentacene OTFT by using Hybrid Oxide of Nd and Hf as Gate Dielectric. , 2018, , .   |    | 0         |
| 121 | Improved electrical properties of MoS <sub>2</sub> transistor with Hf <sub>1-x</sub> Ti <sub>x</sub> O as gate dielectric. , 2019, , .                                |    | 0         |
| 122 | Effects of Gate Electron Concentration on Organic Thin-Film Transistors with Different Pentacene Thicknesses. , 2019, , .   |    | 0         |
| 123 | Effects of Coulomb and Roughness Scatterings on 4H-SiC MOSFET. , 2019, , .  |    | 0         |
| 124 | Improvement of Pentacene Organic Thin-Film Transistor by Using Fluorine Plasma-Treated or Ion-Implanted HfO <sub>2</sub> as Gate Dielectric. , 2019, , .              |    | 0         |